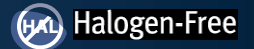


# EPC2052 – Enhancement Mode Power Transistor

 $V_{DS}, 100\text{ V}$ 
 $R_{DS(on)}, 13.5\text{ m}\Omega$ 
 $I_D, 8.2\text{ A}$ 


Revised September 26, 2022

Gallium Nitride's exceptionally high electron mobility and low temperature coefficient allows very low  $R_{DS(on)}$ , while its lateral device structure and majority carrier diode provide exceptionally low  $Q_G$  and zero  $Q_{RR}$ . The end result is a device that can handle tasks where very high switching frequency, and low on-time are beneficial as well as those where on-state losses dominate.



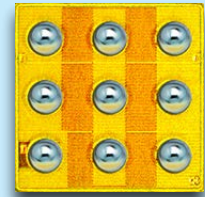
Maximum Ratings			
PARAMETER		VALUE	UNIT
$V_{DS}$	Drain-to-Source Voltage (Continuous)	100	V
	Drain-to-Source Voltage (up to 10,000 5 ms pulses at 150°C)	120	
$I_D$	Continuous ( $T_A = 25^\circ\text{C}$ )	8.2	A
	Pulsed ( $25^\circ\text{C}$ , $T_{PULSE} = 300\ \mu\text{s}$ )	74	
$V_{GS}$	Gate-to-Source Voltage	6	V
	Gate-to-Source Voltage	-4	
$T_J$	Operating Temperature	-40 to 150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-40 to 150	

Thermal Characteristics			
PARAMETER		TYP	UNIT
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2	$^\circ\text{C}/\text{W}$
$R_{\theta JB}$	Thermal Resistance, Junction-to-Board	15	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1)	74	

Note 1:  $R_{\theta JA}$  is determined with the device mounted on one square inch of copper pad, single layer 2 oz copper on FR4 board. See [https://epc-co.com/epc/documents/product-training/Appnote\\_Thermal\\_Performance\\_of\\_eGaN\\_FETs.pdf](https://epc-co.com/epc/documents/product-training/Appnote_Thermal_Performance_of_eGaN_FETs.pdf) for details.

Static Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise stated)						
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-to-Source Voltage	$V_{GS} = 0\text{ V}$ , $I_D = 0.2\text{ mA}$	100			V
$I_{DSS}$	Drain-Source Leakage	$V_{DS} = 80\text{ V}$ , $V_{GS} = 0\text{ V}$ , $T_J = 25^\circ\text{C}$		0.02	0.15	mA
$I_{GSS}$	Gate-to-Source Forward Leakage	$V_{GS} = 5\text{ V}$ , $T_J = 25^\circ\text{C}$		0.01	1.8	mA
		$V_{GS} = 5\text{ V}$ , $T_J = 125^\circ\text{C}$		0.2	4	mA
	Gate-to-Source Reverse Leakage <sup>#</sup>	$V_{GS} = -4\text{ V}$ , $T_J = 25^\circ\text{C}$		0.01	0.18	mA
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$ , $I_D = 3\text{ mA}$	0.8	1.4	2.5	V
$R_{DS(on)}$	Drain-Source On Resistance	$V_{GS} = 5\text{ V}$ , $I_D = 11\text{ A}$		10	13.5	m $\Omega$
$V_{SD}$	Source-Drain Forward Voltage <sup>#</sup>	$I_S = 0.5\text{ A}$ , $V_{GS} = 0\text{ V}$		2.0		V

<sup>#</sup> Defined by design. Not subject to production test.



Die Size: 1.5 x 1.5 mm

EPC2052 eGaN® FETs are supplied in passivated die form with solder bumps.

### Applications

- 48 V Servers
- Lidar/Pulsed Power
- Isolated Power Supplies
- Point of Load Converters
- Class D Audio
- LED Lighting
- Low Inductance Motor Drive

### Benefits

- Higher Switching Frequency – Lower switching losses and lower drive power
- Higher Efficiency – Lower conduction and switching losses, zero reverse recovery losses
- Ultra Small Footprint - Higher power density

Scan QR code or click link below for more information including reliability reports, device models, demo boards!



<https://l.ead.me/EPC2052>

Dynamic Characteristics<sup>#</sup> (T<sub>J</sub> = 25°C unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
C <sub>ISS</sub>	Input Capacitance	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 0 V		441	584	pF
C <sub>RSS</sub>	Reverse Transfer Capacitance			3.2		
C <sub>OSS</sub>	Output Capacitance			195	293	
C <sub>OSS(ER)</sub>	Effective Output Capacitance, Energy Related (Note 2)	V <sub>DS</sub> = 0 to 50 V, V <sub>GS</sub> = 0 V		227		
C <sub>OSS(TR)</sub>	Effective Output Capacitance, Time Related (Note 3)			274		
R <sub>G</sub>	Gate Resistance			0.7		Ω
Q <sub>G</sub>	Total Gate Charge	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 11 A		3.5	4.5	nC
Q <sub>GS</sub>	Gate to Source Charge	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 11 A		1.5		
Q <sub>GD</sub>	Gate to Drain Charge			0.5		
Q <sub>G(TH)</sub>	Gate Charge at Threshold			1.0		
Q <sub>OSS</sub>	Output Charge	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = 50 V		13	20	
Q <sub>RR</sub>	Source-Drain Recovery Charge			0		

# Defined by design. Not subject to production test.

All measurements were done with substrate connected to source.

Note 2: C<sub>OSS(ER)</sub> is a fixed capacitance that gives the same stored energy as C<sub>OSS</sub> while V<sub>DS</sub> is rising from 0 to 50% BV<sub>DSS</sub>.

Note 3: C<sub>OSS(TR)</sub> is a fixed capacitance that gives the same charging time as C<sub>OSS</sub> while V<sub>DS</sub> is rising from 0 to 50% BV<sub>DSS</sub>.

Figure 1: Typical Output Characteristics at 25°C

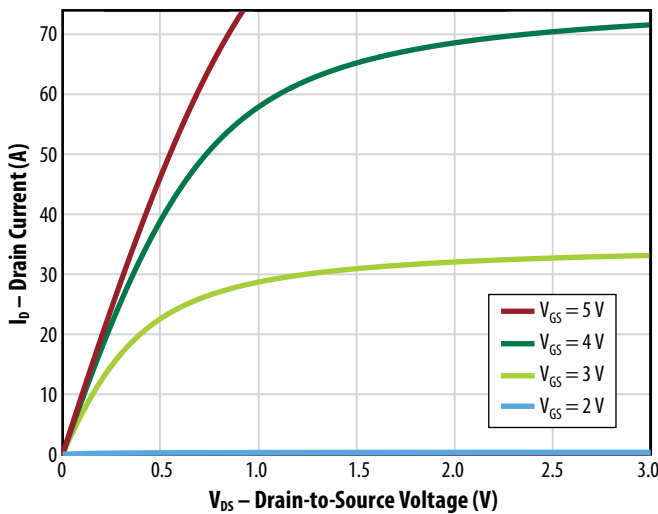


Figure 2: Typical Transfer Characteristics

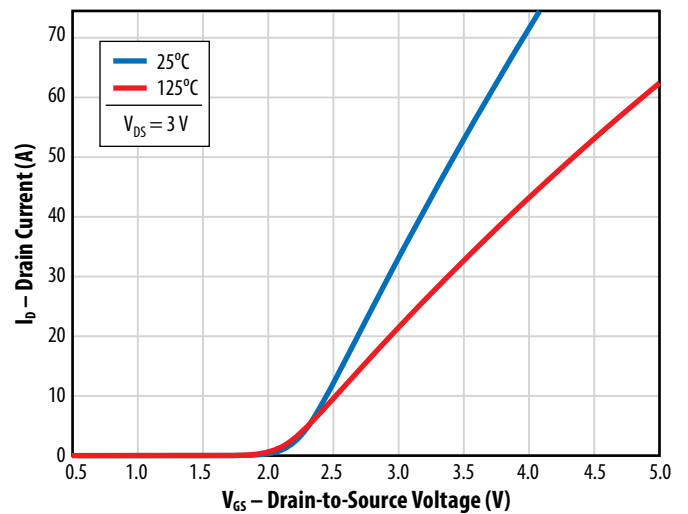


Figure 3: Typical R<sub>DS(on)</sub> vs. V<sub>GS</sub> for Various Currents

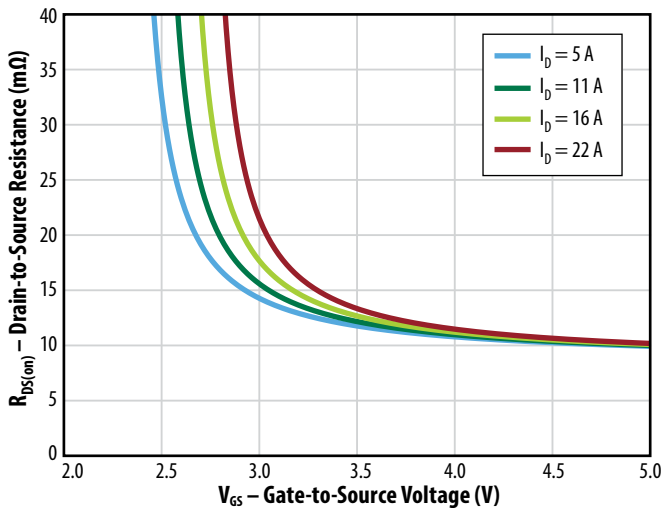


Figure 4: Typical R<sub>DS(on)</sub> vs. V<sub>GS</sub> for Various Temperatures

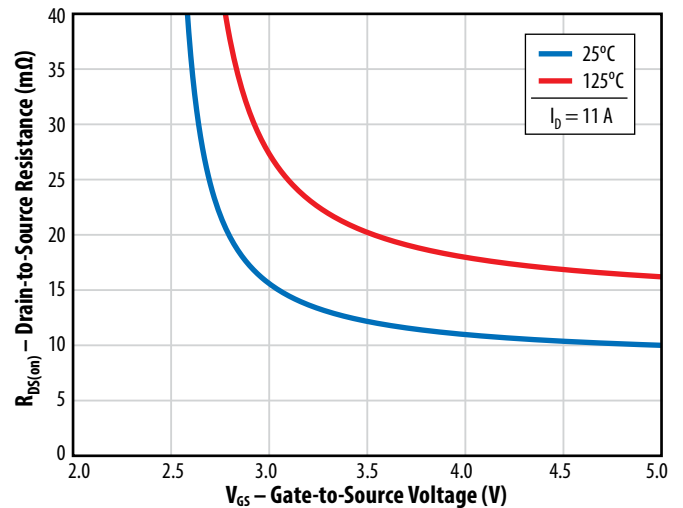


Figure 5a: Typical Capacitance (Linear Scale)

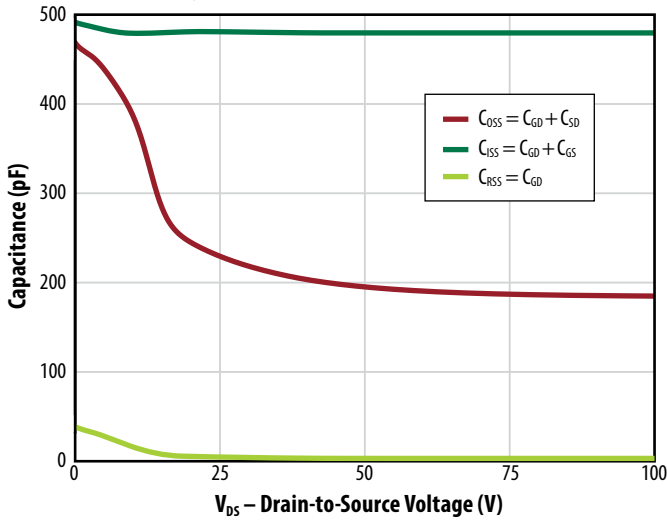


Figure 5b: Typical Capacitance (Log Scale)

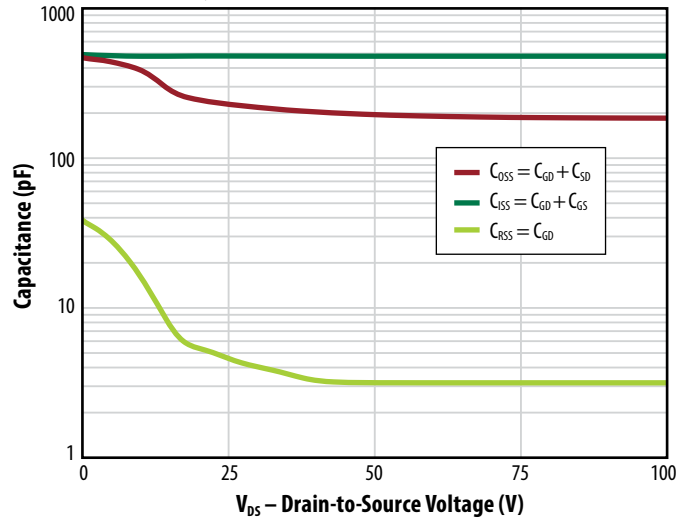


Figure 6: Typical Output Charge and C\_oss Stored Energy

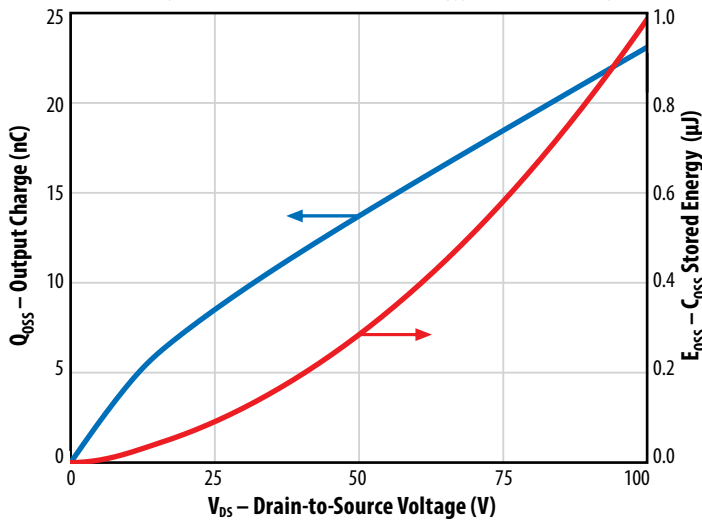


Figure 7: Typical Gate Charge

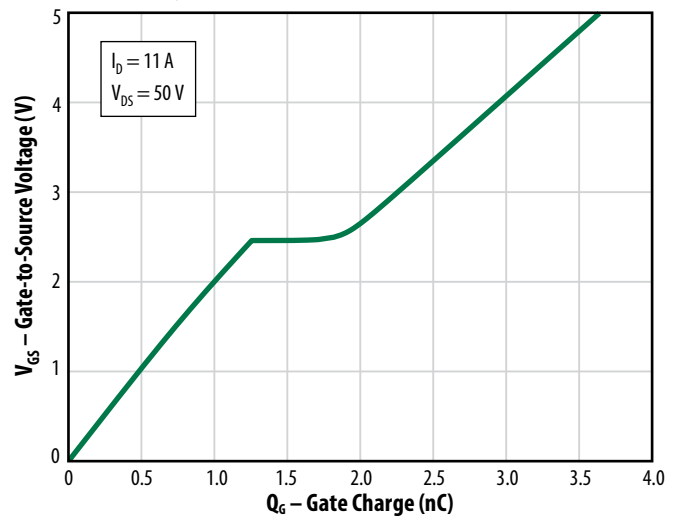


Figure 8: Typical Reverse Drain-Source Characteristics

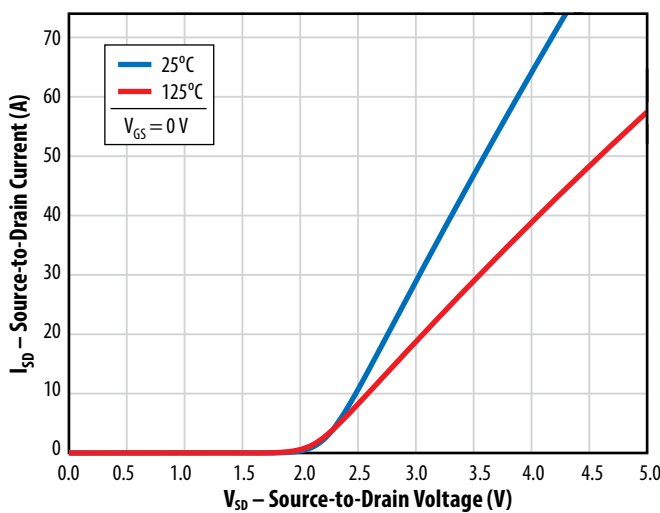
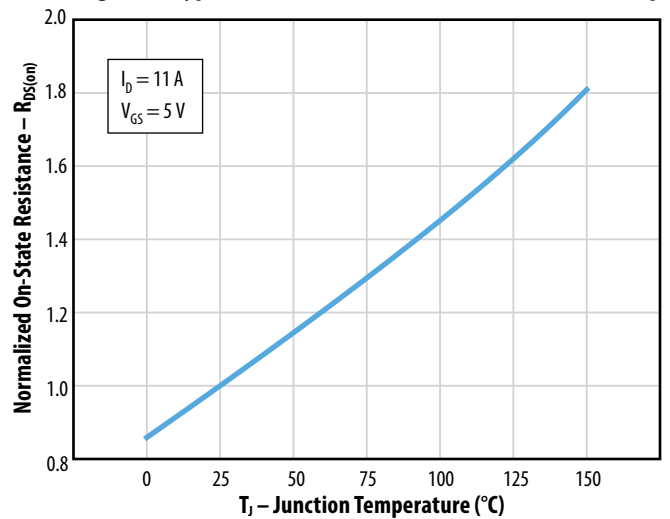


Figure 9: Typical Normalized On-State Resistance vs. Temp.



Negative gate drive voltage increases the reverse drain-source voltage.  
EPC recommends 0V for OFF

Figure 10: Typical Normalized Threshold Voltage vs. Temp.

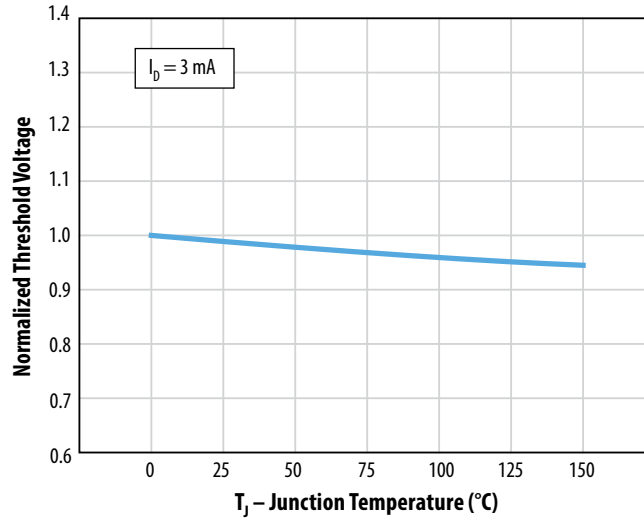


Figure 11: Typical Transient Thermal Response Curves

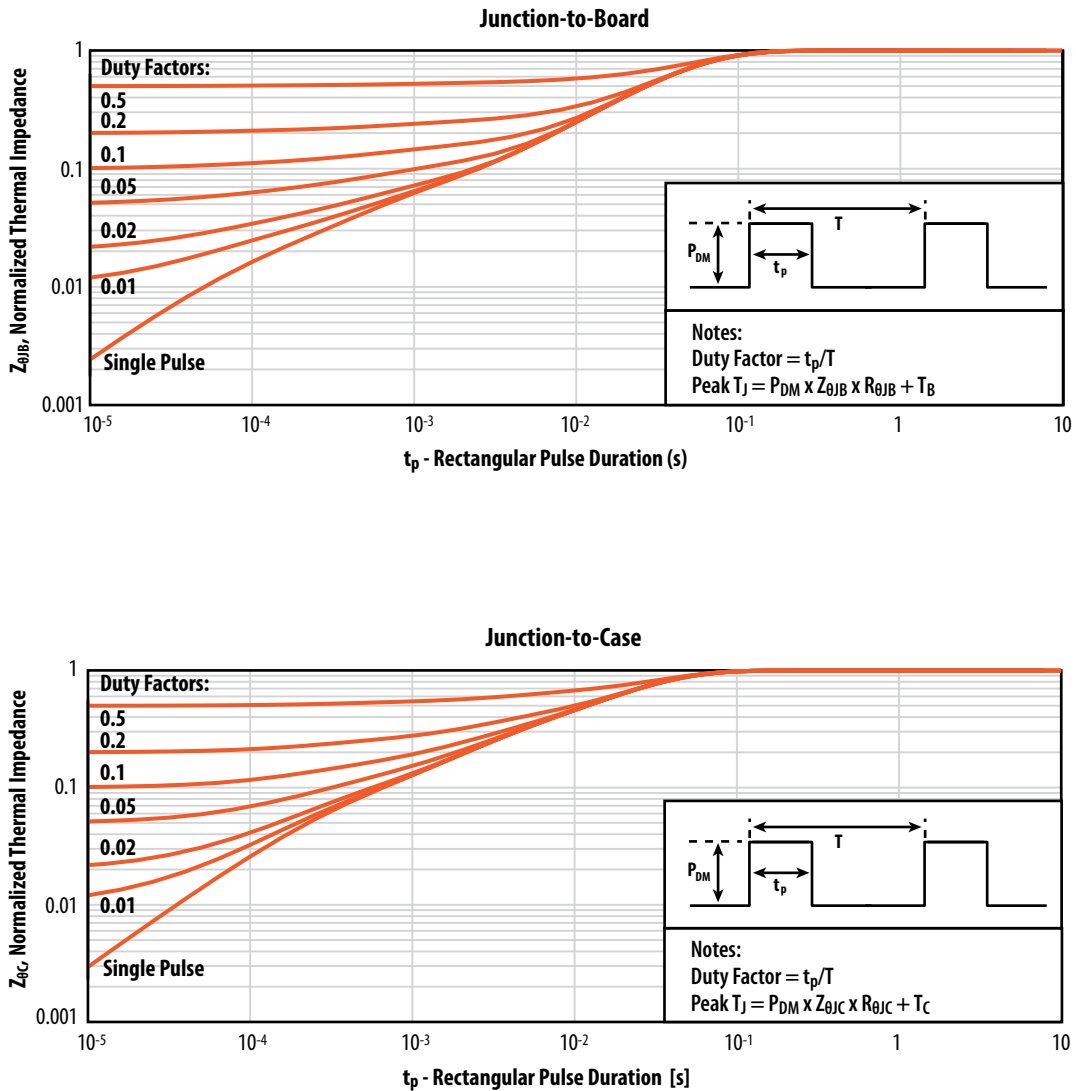
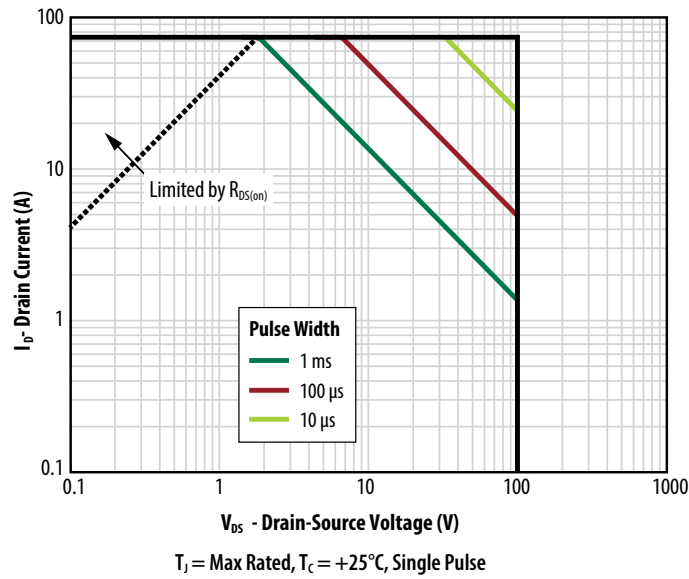
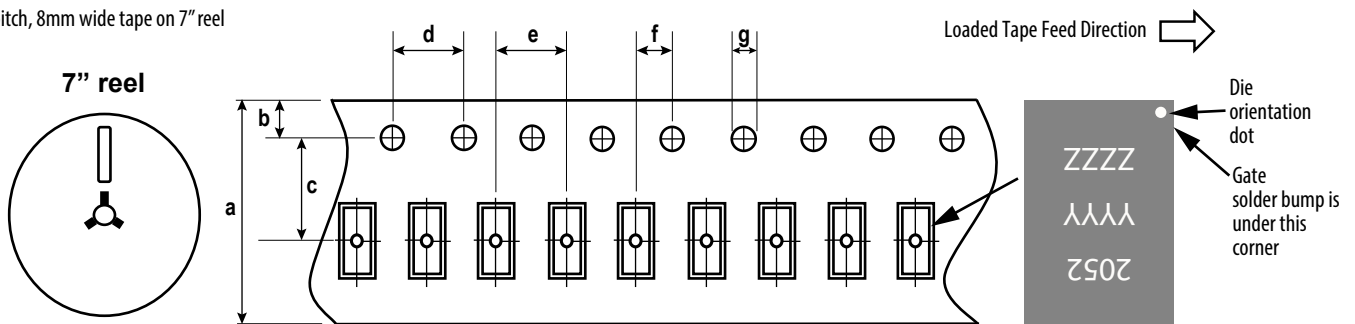


Figure 12: Safe Operating Area



**TAPE AND REEL CONFIGURATION**

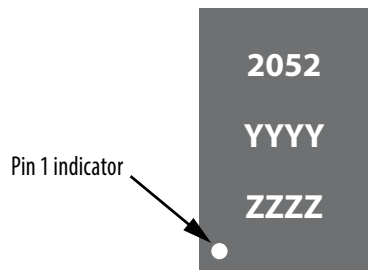
4mm pitch, 8mm wide tape on 7" reel



EPC2052 (note 1)			
Dimension (mm)	target	min	max
a	8.00	7.90	8.30
b	1.75	1.65	1.85
c (see note)	3.50	3.45	3.55
d	4.00	3.90	4.10
e	4.00	3.90	4.10
f (see note)	2.00	1.95	2.05
g	1.5	1.5	1.6

Note 1: MSL 1 (moisture sensitivity level 1) classified according to IPC/JEDEC industry standard.  
 Note 2: Pocket position is relative to the sprocket hole measured as true position of the pocket, not the pocket hole.

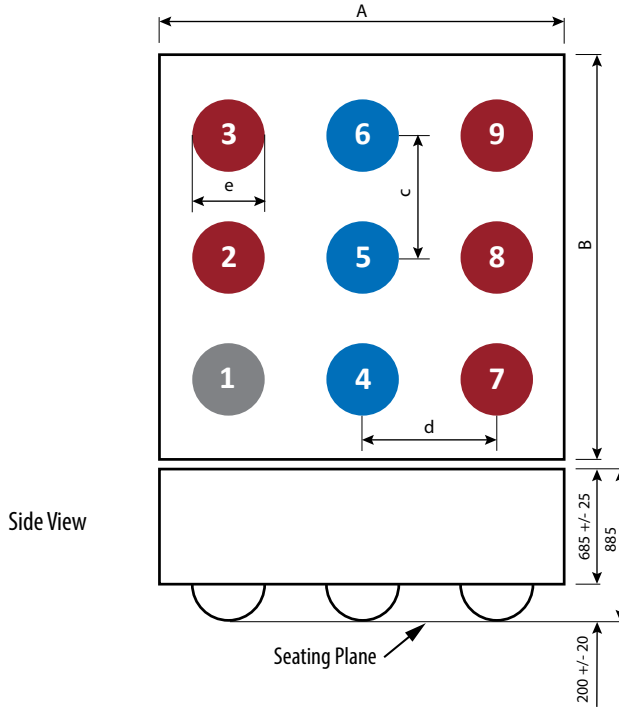
**DIE MARKINGS**



Part Number	Laser Markings		
	Part # Marking Line 1	Lot_Date Code Marking line 2	Lot_Date Code Marking Line 3
EPC2052	2052	YYYY	ZZZZ

**DIE OUTLINE**

Solder Bump View



DIM	MICROMETERS		
	MIN	Nominal	MAX
A	1470	1500	1530
B	1470	1500	1530
c		450	
d		500	
e	238	264	290

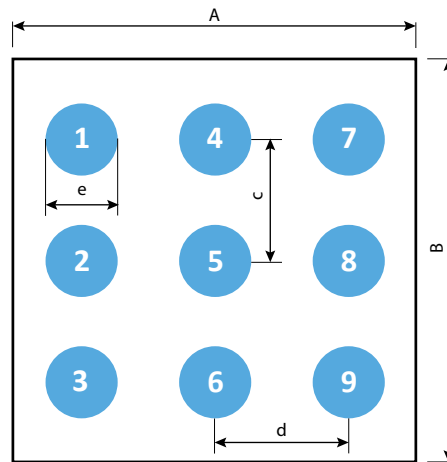
Pad 1 is Gate;

Pads 2, 3, 7, 8, 9 are Source;

Pads 4, 5, 6 are Drain.

**RECOMMENDED LAND PATTERN**

(units in  $\mu\text{m}$ )



DIM	MICROMETERS
A	1500
B	1500
c	450
d	500
e	230

Pad 1 is Gate;

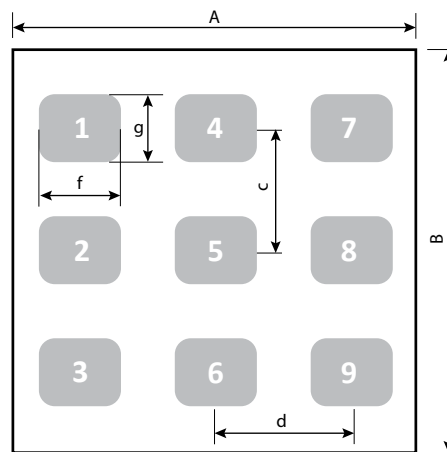
Pads 2, 3, 7, 8, 9 are Source;

Pads 4, 5, 6 are Drain.

**RECOMMENDED STENCIL DRAWING**

(measurements in  $\mu\text{m}$ )

Additional assembly resources available at <https://epc-co.com/epc/design-support>



DIM	MICROMETERS
A	1500
B	1500
c	450
d	500
f	300
g	250

Pad 1 is Gate;

Pads 2, 3, 7, 8, 9 are Source;

Pads 4, 5, 6 are Drain.

Recommended stencil should be 4 mil (100  $\mu\text{m}$ ) thick, must be laser cut, opening per drawing.

The corner has a radius of R60. Intended for use with SAC305 Type 4 solder, reference 88.5% metals content.

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